

	Type	Hits	Search Text	DBs	Time Stamp
1	IS&R	1612	(257/369,371,372).CCLS.	USPAT	2006/02/04 14:50
2	IS&R	496	(257/255,627,628).CCLS.	USPAT	2006/02/04 14:50
3	IS&R	1578	(257/369,371,372).CCLS.	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/02/04 14:50
4	IS&R	276	(257/255,627,628).CCLS.	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/02/04 15:44
5	BRS	6	compression adj strain with channel	USPAT	2006/02/04 15:52
6	BRS	25	compression adj strain with channel	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/02/04 16:00
7	BRS	78	tensile adj strain with channel	USPAT	2006/02/04 16:00
8	BRS	158	tensile adj strain with channel	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/02/04 16:00
9	BRS	45	(CMOS complementary) and (crystal adj (axis plane)) and strain	USPAT	2006/02/06 06:26
10	BRS	58	(CMOS complementary) and (crystal adj (axis plane)) and strain	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/02/06 06:26
11	IS&R	1140	(438/199,223,224,227,228).CCLS.	USPAT	2006/02/06 11:57
12	BRS	4	S74 and (crystal adj axis)	USPAT	2006/02/06 11:57

	Type	Hits	Search Text	DBs	Time Stamp
13	IS&R	789	(438/199,223,224,227,228).CCLS.	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/02/06 11:57
14	BRS	0	S74 and (crystal adj axis)	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB	2006/02/06 11:57
15	BRS	2	((transistor transistors gate gates) and (crystal adj axis) and (tensile compression compressive) adj stress).clm.	US-PGPUB	2006/02/06 11:58